



A grayscale micrograph of a semiconductor device, likely a power MOSFET, showing a central gate region surrounded by various layers and structures. The image is divided into four quadrants by a central cross. Labels with arrows point to specific features: 'Bias grid' points to the top-left quadrant; 'Aluminium' points to the top-left quadrant; 'Reduced p-spray' points to the central cross; 'Bias dot' points to the top-right quadrant; 'p-Implant' points to the top-right quadrant; 'Full p-spray dose' points to the central cross; 'Bump (In)' points to the bottom-right quadrant; and 'Contact via' points to the bottom-right quadrant.

Bias grid

Bias dot

Aluminium

p-Implant

Reduced p-spray

Full p-spray dose

Bump (In)

Contact via